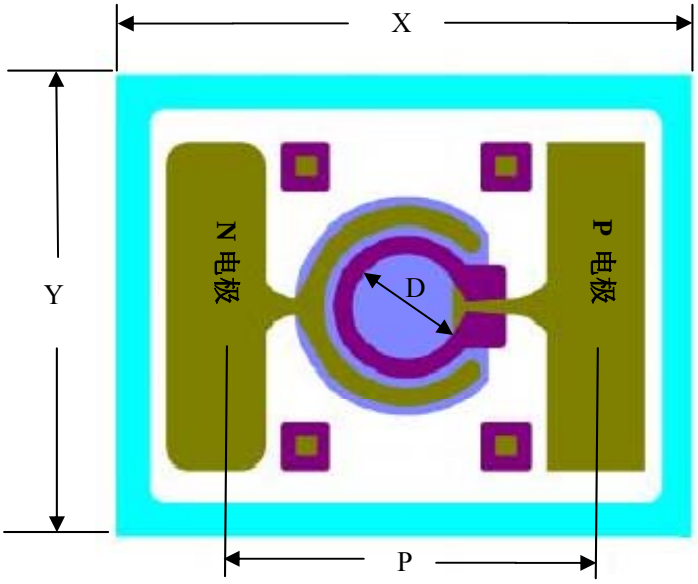
S-15BMPD06-G InGaAs/InP Photo Diode 芯片特性参数

♦ Physical Parameters:



Die Dimension		Pad Pitch (P)	Pad Dimension	Aperture Diameter (D)	Die Thickness
X	Y				
350μm	280μm	230μm	200μm×60μm	60μm	150μm

♦ Specifications（T=25^{0}C）:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Wavelength Range			910	1310/1550	1650	nm
Dark Current	I_D	V_R=5V		2	5	nA
Capacitance	C	V_R=5V		0.20	0.25	pF
Responsivity	R_e	V_R=5V λ=1550nm	0.90	0.95		A/W
-3dB Bandwidth	BW	V_R=5V λ=1550nm	8	10		GHz